

HIP2105, HIP2106A

Low Voltage Driver for Synchronous Rectification

FN8999
Rev.1.00
Jun 6, 2018

The [HIP2105](#) and [HIP2106A](#) are high frequency MOSFET drivers optimized to drive two N-channel power MOSFETs in a synchronous buck converter topology. The HIP2105 has HI/LI inputs and the HIP2106A has a single PWM input. Both these drivers, combined with Renesas multi-phase buck PWM controllers, form a complete single-stage core-voltage regulator solution with high-efficiency performance at high switching frequency for advanced microprocessors.

The HIP2105 and HIP2106A are biased by a single low voltage supply (5V), minimizing driver switching losses in high MOSFET gate capacitance and high switching frequency applications. Each driver is capable of driving a 3nF load with less than 15ns rise/fall time.

Bootstrapping of the upper gate driver is implemented using an internal low forward voltage drop diode, reducing implementation cost, complexity, and allowing the use of higher performance, cost effective N-channel MOSFETs. Adaptive shoot-through protection on the HIP2106A is integrated to prevent both MOSFETs from conducting simultaneously.

The HIP2105 and HIP2106A feature a 4A typical sink current for the lower gate driver, enhancing the lower MOSFET gate hold-down capability during PHASE node rising edge, preventing power loss caused by the self turn-on of the lower MOSFET due to the high dV/dt of the switching node.

The HIP2106A also features an input that recognizes a high-impedance state, working together with Renesas multi-phase 3.3V or 5V PWM controllers to prevent negative transients on the controlled output voltage when operation is suspended. This feature eliminates the need for the Schottky diode that may be used in a power system to protect the load from negative output voltage damage.

Features

- Adaptive shoot-through protection (HIP2106A only)
- HI and LI inputs (HIP2105 only)
- 0.4Ω ON-resistance and 4A sink current capability
- Low tri-state hold-off time (20ns) (HIP2106A only)
- Supports 3.3V and 5V HI/LI or PWM input
- Power-On Reset (POR)
- Dual Flat No-Lead (DFN) package
 - Compliant to JEDEC PUB95 MO-220 QFN-Quad Flat No Leads - product outline
 - Near chip-scale package footprint; improves PCB efficiency and thinner in profile

Applications

- Wireless chargers
- High frequency low profile high efficiency DC/DC converters
- High current low voltage DC/DC converters
- E-cigarette

Related Literature

For a full list of related documents, visit our website

- [HIP2105](#) and [HIP2106A](#) product pages

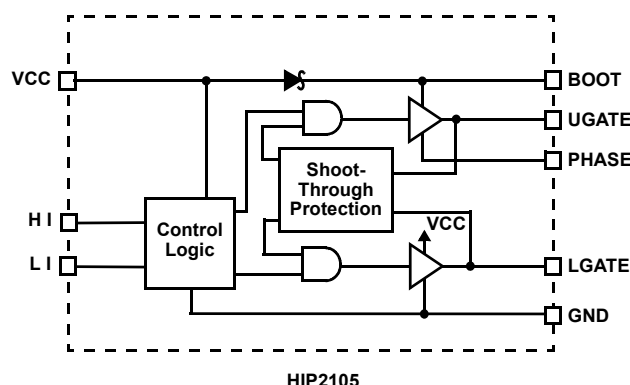
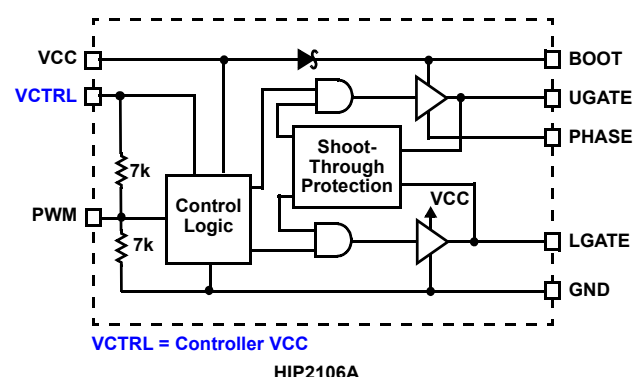


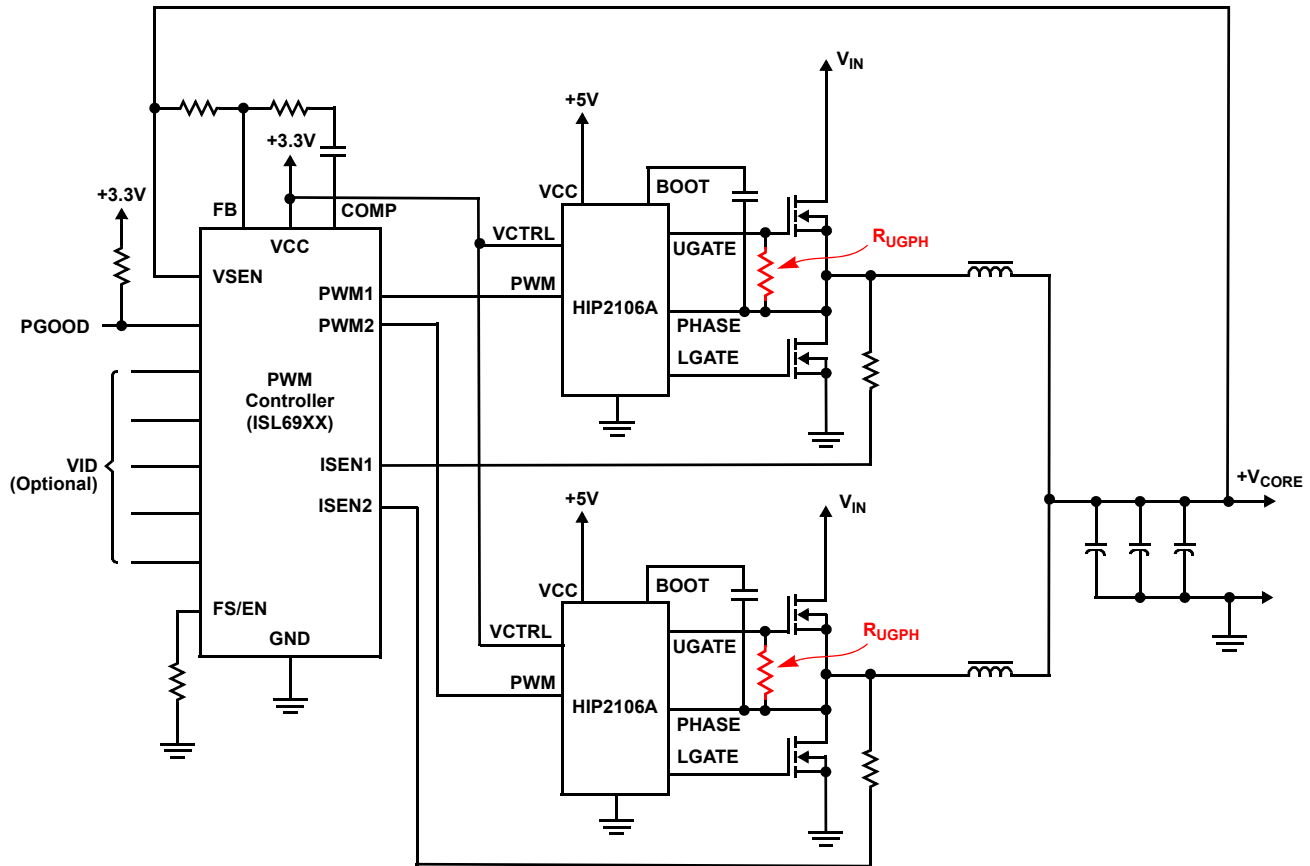
Figure 1. Block Diagrams

Contents

1.	Overview	3
1.1	Typical Applications	3
1.2	Ordering Information	4
1.3	Pin Configurations	5
1.4	Pin Descriptions	5
2.	Specifications	6
2.1	Absolute Maximum Ratings	6
2.2	Thermal Information	6
2.3	Recommended Operating Conditions	6
2.4	Electrical Specifications	7
2.5	Timing Test Setups	8
2.6	Timing Diagrams	9
3.	Device Information	10
3.1	Operation and Adaptive Shoot-Through Protection (HIP2106A)	10
3.2	HI/LI Inputs (HIP2105)	10
3.3	Bootstrap Considerations	11
3.4	Power Dissipation	11
4.	Application Information	13
4.1	MOSFET Selection	13
4.2	Layout Considerations	13
4.3	Upper MOSFET Self Turn-On Effects at Startup	14
5.	Revision History	15
6.	Package Outline Drawing	16

1. Overview

1.1 Typical Applications



R_{UGPH} is required for special power sequencing applications
(see ["Upper MOSFET Self Turn-On Effects at Startup" on page 14](#))

Figure 2. Multi-Phase Converter Using HIP2106A Gate Drivers

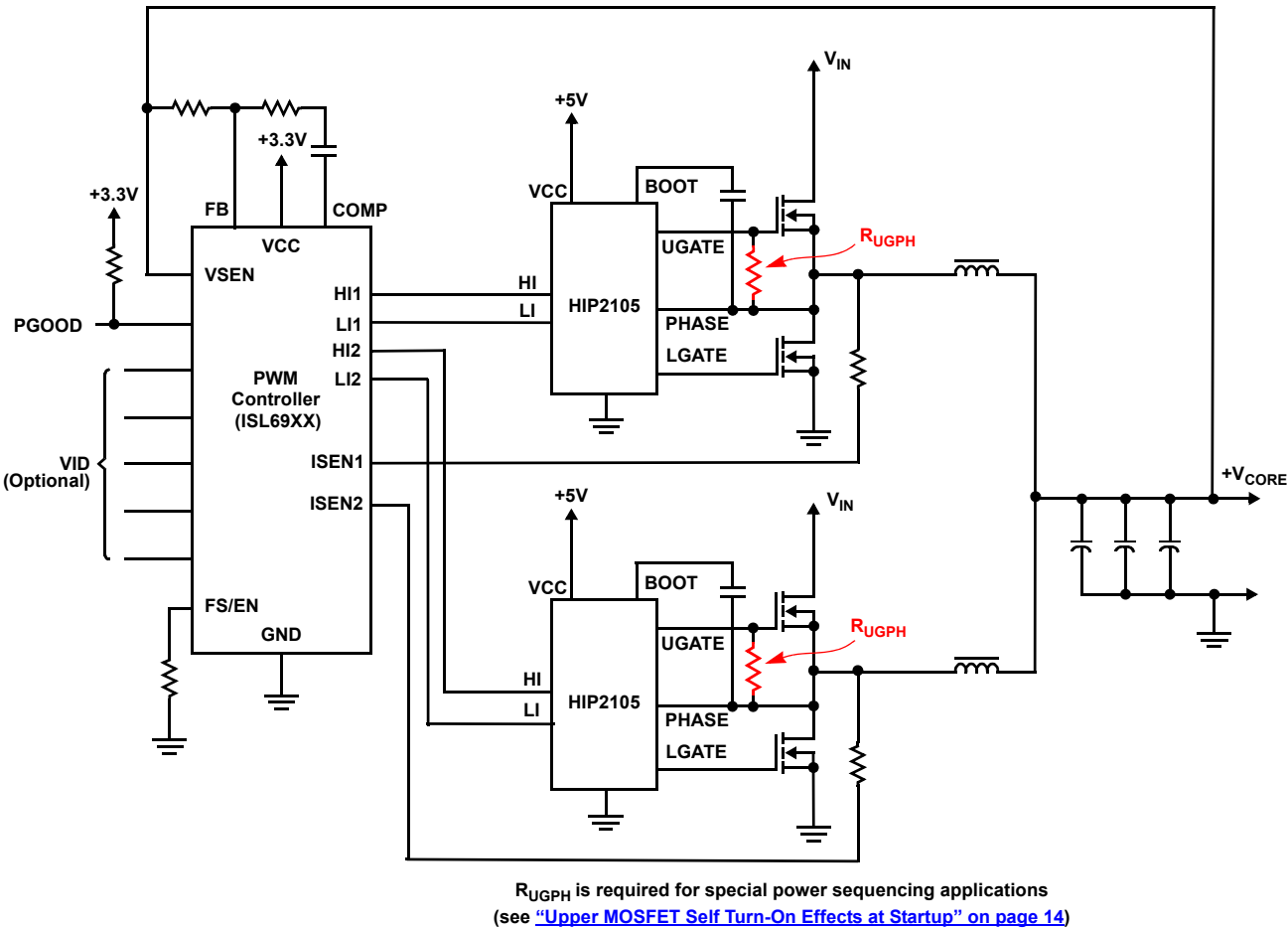


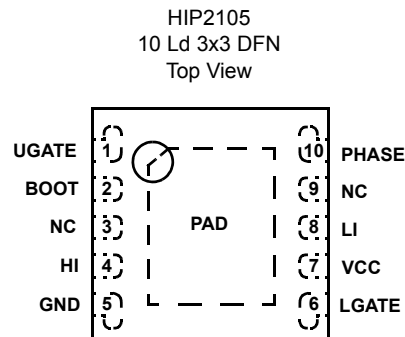
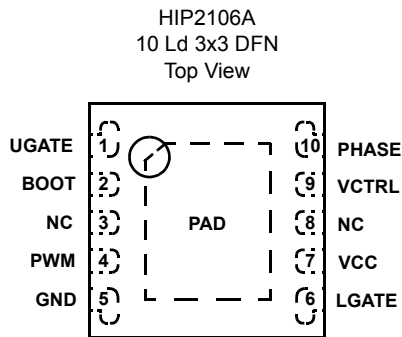
Figure 3. Multi-Phase Converter Using HIP2105 Gate Drivers

1.2 Ordering Information

Part Number (Notes 2, 3)	Part Marking	Temperature Range (°C)	Tape and Reel (Units) (Note 1)	Package	Pkg. Dwg. #
HIP2106AIRZ	06IZ	-40 to +85	-	10 Ld 3x3 DFN	L10.3x3C
HIP2106AIRZ-T	06IZ	-40 to +85	6k	10 Ld 3x3 DFN	L10.3x3C
HIP2105FRZ	05FZ	-40 to +125	-	10 Ld 3x3 DFN	L10.3x3C
HIP2105FRZ-T	05FZ	-40 to +125	6k	10 Ld 3x3 DFN	L10.3x3C
HIP2105-6MBEVAL1Z	HIP2105/6A Mother Board				
HIP2105DBEVAL1Z	HIP2105 Daughter Board				
HIP2106ADBEVAL1Z	HIP2106A Daughter Board				

- Notes:
- 1. Refer to [TB347](#) for details about reel specifications.
 - 2. These Pb-free plastic packaged products employ special Pb-free material sets, molding compounds/die attach materials, and 100% matte tin plate plus anneal (e3 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations). Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.
 - 3. For Moisture Sensitivity Level (MSL), see the [HIP2105](#) and [HIP2106A](#) product information pages. For more information about MSL, refer to [TB363](#).

1.3 Pin Configurations



1.4 Pin Descriptions

Pin Name	HIP2106A Pin #	HIP2105 Pin #	Description
UGATE	1	1	Upper gate drive output. Connect to the gate of the high-side N-channel power MOSFET. A gate resistor is never recommended on this pin, because it interferes with the operation shoot-through protection circuitry. Gate resistor avoidance only applies to HIP2106A. HIP2105 does not have adaptive shoot-through protection.
BOOT	2	2	Floating bootstrap supply pin for the upper gate drive. Connect a bootstrap capacitor between this pin and the PHASE pin. The bootstrap capacitor provides the charge used to turn on the upper MOSFET. See “Bootstrap Considerations” on page 11 for guidance in choosing the appropriate capacitor value.
NC	3, 8	3, 9	No connect.
PWM	4	-	The PWM signal (for HIP2106A) is the control input for the driver. The PWM signal can enter three distinct states during operation, see “PWM Input and Threshold Control (HIP2106A)” on page 10 for further details. Connect this pin to the PWM output of the controller.
HI	-	4	The HI signal (for the HIP2105) is the input drive for the high side gate drive output.
GND	5	5	Ground pin. All signals are referenced to this node.
LGATE	6	6	Lower gate drive output. Connect to the gate of the low-side N-channel power MOSFET. A gate resistor is never recommended on this pin, because it interferes with the operation shoot-through protection circuitry. Gate resistor avoidance only applies to HIP2106A. HIP2105 does not have adaptive shoot-through protection.
VCC	7	7	Connect this pin to a +5V bias supply. Locally bypass with a high quality ceramic capacitor to ground.
LI	-	8	This pin is the input drive for the low-side gate output.
VCTRL	9	-	This VCTRL pin (for HIP2106A) sets the PWM logic threshold. Connect this pin to 3.3V source for 3.3V PWM input or pull it to 5V source for 5V PWM input.
PHASE	10	10	Connect this pin to the source of the upper MOSFET. This pin provides the return path for the upper gate driver current.
Thermal Pad	Pad	Pad	The metal pad underneath the center of the IC is a thermal substrate. The PCB “thermal land” design for this exposed die pad should include vias that drop down and connect to one or more buried copper plane(s). This combination of vias for vertical heat escape and buried planes for heat spreading allows the DFN to achieve its full thermal potential. This pad should be either grounded or floating, and it should not be connected to other nodes. Refer to TB389 for design guidelines.

2. Specifications

2.1 Absolute Maximum Ratings

Parameter	Minimum	Maximum	Unit
Supply Voltage (V_{CC} , V_{CTRL})	-0.3	7	V
Input Voltage (V_{EN} , V_{PWM} , V_{HI} , V_{LI})	-0.3	$V_{CC} + 0.3$	V
BOOT Voltage ($V_{BOOT-GND}$)	-0.3	25 (DC) or 36 (<200ns)	V
BOOT to PHASE Voltage ($V_{BOOT-PHASE}$)	-0.3	7 (DC)	V
	-0.3	9 (<10ns)	V
PHASE Voltage	GND - 0.3	25 (DC)	V
	GND - 8 (<20ns Pulse Width, 10 μ J)	30 (<100ns)	V
UGATE Voltage	$V_{PHASE} - 0.3$ (DC)	V_{BOOT}	V
	$V_{PHASE} - 5$ (<20ns Pulse Width, 10 μ J)	V_{BOOT}	V
LGATE Voltage	GND - 0.3 (DC)	$V_{CC} + 0.3$	V
	GND - 2.5 (<20ns Pulse Width, 5 μ J)	$V_{CC} + 0.3$	V
ESD Rating	Value		Unit
Human Body Model (Tested per JS-001-2017)	2		kV
Charged Device Model (Tested per JS-002-2014)	2		kV
Latch-Up (Tested per JESD78E; Class 2, Level A)	100		mA

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions can adversely impact product reliability and result in failures not covered by warranty.

2.2 Thermal Information

Thermal Resistance (Typical)	θ_{JA} ($^{\circ}\text{C}/\text{W}$)	θ_{JC} ($^{\circ}\text{C}/\text{W}$)
DFN Package (Notes 4, 5)	48	7

Notes:

- θ_{JA} is measured in free air with the component mounted on a high-effective thermal conductivity test board with "direct attach" features. See [TB379](#).
- For θ_{JC} , the "case temp" location is the center of the exposed metal pad on the package underside.

Parameter	Minimum	Maximum	Unit
Maximum Junction Temperature		+150	$^{\circ}\text{C}$
Maximum Storage Temperature Range	-65	+150	$^{\circ}\text{C}$
Pb-Free Reflow Profile	Refer to TB493		

2.3 Recommended Operating Conditions

Parameter	Minimum	Maximum	Unit
Ambient Temperature Range (HIP2106A)	-40	+85	$^{\circ}\text{C}$
Ambient Temperature Range (HIP2105)	-40	+125	$^{\circ}\text{C}$
Maximum Operating Junction Temperature		+125	$^{\circ}\text{C}$
Supply Voltage, V_{CC}	4.5	5.5	V

2.4 Electrical Specifications

Recommended operating conditions, $V_{CC} = 5V \pm 10\%$, unless otherwise specified, **Boldface limits apply across the operating temperature range -40°C to $+85^{\circ}\text{C}$ for HIP2106A and -40°C to $+125^{\circ}\text{C}$ for HIP2105.**

Parameter	Symbol	Test Conditions	Min (Note 7)	Typ	Max (Note 7)	Unit
V_{CC} Supply Current						
Bias Supply Current - HIP2106A	I _{VCC}	PWM pin floating, V _{VCC} = 5V	-	190	-	μA
Bias Supply Current - HIP2105	I _{VCC}	HI/LI pin floating, V _{VCC} = 5V	-	80	-	μA
POR Rising			-	3.4	4.2	V
POR Falling			2.2	3.1	-	V
Hysteresis			-	300	-	mV
VCTRL Input (HIP2106A only)						
Rising Threshold			-	2.75	2.90	V
Falling Threshold			2.4	2.65	-	V
PWM Input (HIP2106A only)						
Sinking Impedance	R _{PWM_SNK}		-	3.5	-	kΩ
Source Impedance	R _{PWM_SRC}		-	3.5	-	kΩ
Tri-State Lower Threshold		V _{VCTRL} = 3.3V (-110mV hysteresis)	-	1.1	-	V
		V _{VCTRL} = 5V (-250mV hysteresis)	-	1.5	-	V
Tri-State Upper Threshold		V _{VCTRL} = 3.3V (+110mV hysteresis)	-	1.9	-	V
		V _{VCTRL} = 5V (+250mV hysteresis)	-	3.25	-	V
Tri-State Shutdown Hold-Off Time	t _{TSSHD}	t _{PDLU} or t _{PDLL} + gate falling time	-	20	-	ns
HI/LI Input (HIP2105 only)						
V _{IH} and V _{IL} Rising	V _{IH}	V _{DD} = 4.5V	1.3	1.65	2	V
		V _{DD} = 5.0V	1.4	1.75	2.1	
		V _{DD} = 5.5V	1.5	1.9	2.2	V
V _{IH} and V _{IL} Falling	V _{IL}	V _{DD} = 4.5V	0.9	1.1	1.45	V
		V _{DD} = 5.0V	0.95	1.2	1.55	
		V _{DD} = 5.5V	1.05	1.3	1.65	V
Switching Time (HIP2106A, See Figure 6 on page 9)						
UGATE Rise Time (Note 6)	t _{RU}	V _{VCC} = 5V, 3nF load	-	8	-	ns
LGATE Rise Time (Note 6)	t _{RL}	V _{VCC} = 5V, 3nF load	-	8	-	ns
UGATE Fall Time (Note 6)	t _{FU}	V _{VCC} = 5V, 3nF load	-	8	-	ns
LGATE Fall Time (Note 6)	t _{FL}	V _{VCC} = 5V, 3nF load	-	4	-	ns
UGATE Turn-Off Propagation Delay	t _{PDLU}	V _{VCC} = 5V, outputs unloaded	-	20	-	ns
LGATE Turn-Off Propagation Delay	t _{PDLL}	V _{VCC} = 5V, outputs unloaded	-	15	-	ns
UGATE Turn-On Propagation Delay	t _{PDHU}	V _{VCC} = 5V, outputs unloaded	-	19	-	ns
LGATE Turn-On Propagation Delay	t _{PDHL}	V _{VCC} = 5V, outputs unloaded	-	18	-	ns
Tri-State to UG/LG Rising Propagation Delay	t _{PTS}	V _{VCC} = 5V, outputs unloaded	-	30	-	ns
Switching Time (HIP2105, See Figure 7 on page 9)						
UGATE Rise Time (Note 6)	t _{RU}	V _{VCC} = 5V, 3nF load	-	15	-	ns
LGATE Rise Time (Note 6)	t _{RL}	V _{VCC} = 5V, 3nF load	-	10	-	ns
UGATE Fall Time (Note 6)	t _{FU}	V _{VCC} = 5V, 3nF load	-	15	-	ns

Recommended operating conditions, $V_{CC} = 5V \pm 10\%$, unless otherwise specified. **Boldface limits apply across the operating temperature range -40°C to $+85^{\circ}\text{C}$ for HIP2106A and -40°C to $+125^{\circ}\text{C}$ for HIP2105.**

Parameter	Symbol	Test Conditions	Min (Note 7)	Typ	Max (Note 7)	Unit
LGATE Fall Time (Note 6)	t_{FL}	$V_{VCC} = 5V$, 3nF load	-	6	-	ns
HI to UGATE Falling Propagation Delay	t_{PDFU}	$V_{VCC} = 5V$, outputs unloaded	-	35	-	ns
LI to LGATE Falling Propagation Delay	t_{PDFL}	$V_{VCC} = 5V$, outputs unloaded	-	20	-	ns
HI to UGATE Rising Propagation Delay	t_{PDRU}	$V_{VCC} = 5V$, outputs unloaded	-	29	-	ns
LI to LGATE Rising Propagation Delay	t_{PDRL}	$V_{VCC} = 5V$, outputs unloaded	-	15	-	ns
Turn-On/Off Propagation Mismatch (HO rising to LO falling)	t_{MHRF}	$V_{VCC} = 5V$, outputs unloaded	-	9	-	ns
Turn-On/Off Propagation Mismatch (LO rising to HO falling)	t_{MLRF}	$V_{VCC} = 5V$, outputs unloaded	-	20	-	ns
Output (Note 6)						
Upper Drive Source Resistance	r_{UG_SRC}	250mA source current	-	1.0	2.5	Ω
Upper Drive Sink Resistance	r_{UG_SNK}	250mA sink current	-	1.0	2.5	Ω
Lower Drive Source Resistance	r_{LG_SRC}	250mA source current	-	1.0	2.5	Ω
Lower Drive Sink Resistance	r_{LG_SNK}	250mA sink current	-	0.4	1.0	Ω

Notes:

6. Limits established by characterization and are not production tested.

7. Compliance to datasheet limits is assured by one or more methods: production test, characterization, and/or design.

2.5 Timing Test Setups

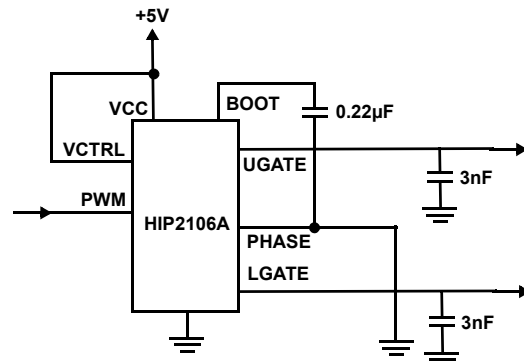


Figure 4. HIP2106A Rise/Fall Timing Test Setup

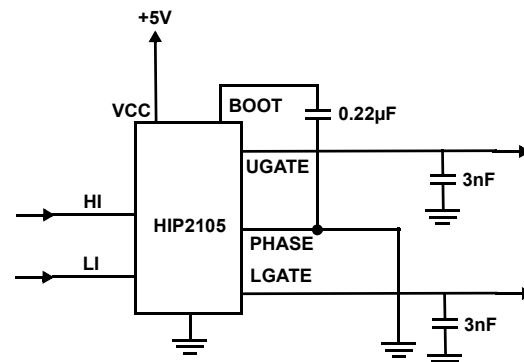


Figure 5. HIP2105 Rise/Fall Timing Test Setup

2.6 Timing Diagrams

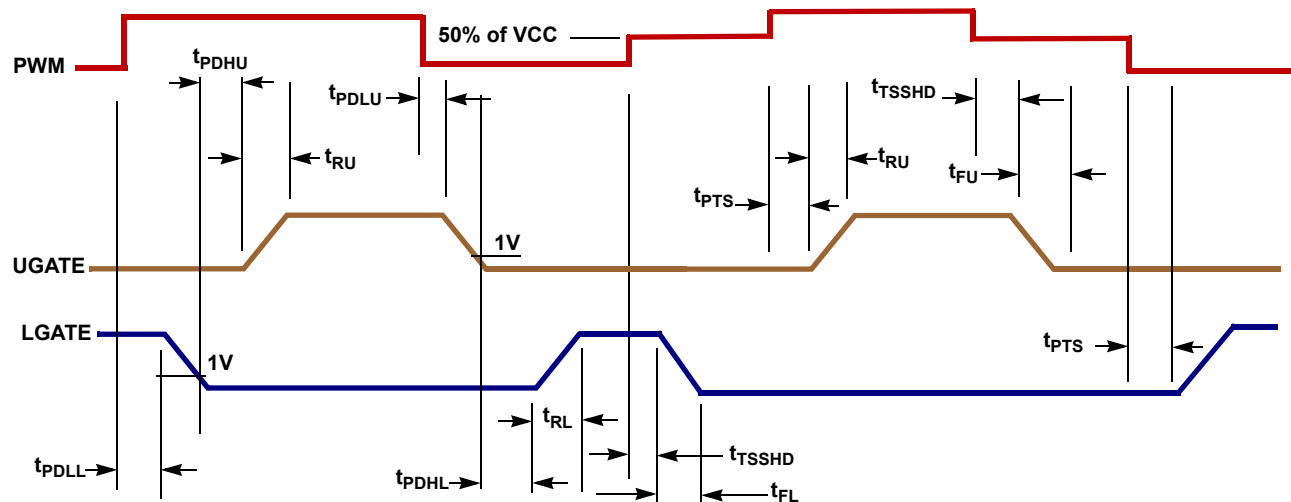


Figure 6. HIP2106A Timing Diagram

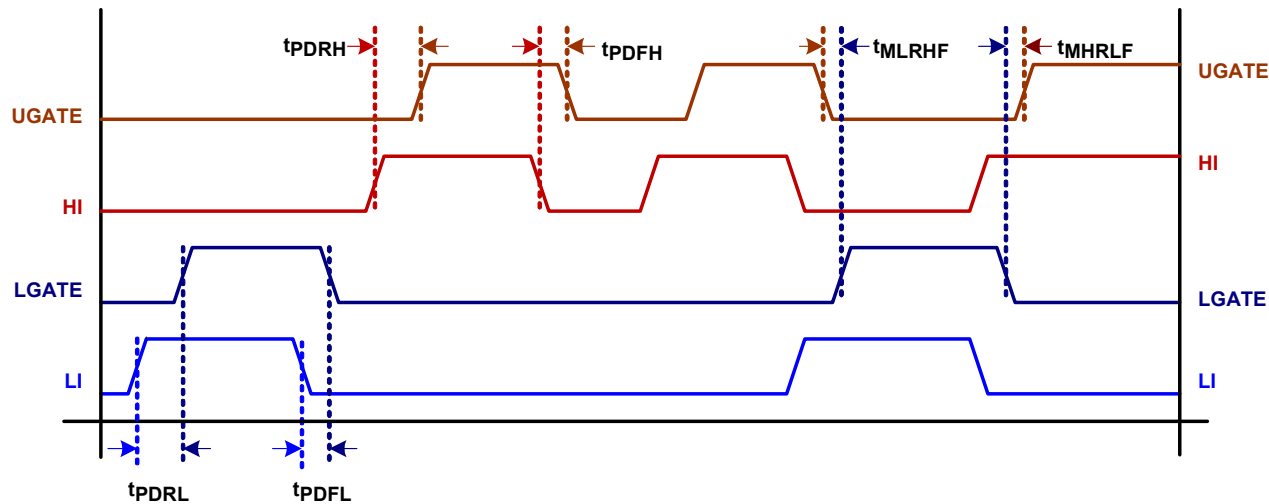


Figure 7. HIP2105 Timing Diagram

3. Device Information

3.1 Operation and Adaptive Shoot-Through Protection (HIP2106A)

Designed for high speed switching, the HIP2106A MOSFET driver controls both high-side and low-side N-channel FETs from one externally provided PWM signal.

A rising transition on PWM initiates the turn-off of the lower MOSFET (see [Figure 4 on page 8](#)). After a short propagation delay (t_{PDLL}), the lower gate begins to fall. Typical fall times (t_{FL}) are provided in the “Electrical Specifications” table on [page 7](#). Adaptive shoot-through circuitry monitors the LGATE voltage and turns on the upper gate following a short delay time (t_{PDHU}) after the LGATE voltage drops below $\sim 1V$. The upper gate drive then begins to rise (t_{RU}) and the upper MOSFET turns on.

A falling transition on PWM indicates the turn-off of the upper MOSFET and the turn-on of the lower MOSFET. A short propagation delay (t_{PDLU}) is encountered before the upper gate begins to fall (t_{FU}). The adaptive shoot-through circuitry monitors the UGATE-PHASE voltage and turns on the lower MOSFET after a short delay time, t_{PDHL} , after the upper MOSFET’s gate voltage drops below $1V$. The lower gate then rises (t_{RL}), turning on the lower MOSFET. These methods prevent both the lower and upper MOSFETs from conducting simultaneously (shoot-through), while adapting the dead time to the gate charge characteristics of the MOSFETs being used.

This driver is optimized for voltage regulators with a large step down ratio. The lower MOSFET is usually sized larger compared to the upper MOSFET because the lower MOSFET conducts for a longer time during a switching period. The lower gate driver is therefore sized much larger to meet this application requirement. The 0.4Ω ON-resistance and 4A sink current capability enable the lower gate driver to absorb the current injected into the lower gate through the drain-to-gate capacitor of the lower MOSFET and help prevent shoot-through caused by the self turn-on of the lower MOSFET due to high dV/dt of the switching node.

3.1.1 PWM Input and Threshold Control (HIP2106A)

A unique feature of the HIP2106A is the programmable PWM logic threshold set by the control pin (VCTRL) voltage. The VCTRL pin should connect to the VCC of the controller, thus the PWM logic threshold follows the voltage level of the controller. For 5V applications, this pin can tie to the driver VCC and simplify the routing.

The HIP2106A also features adaptable tri-state PWM input. When the PWM signal enters the shutdown window, either MOSFET previously conducting is turned off. If the PWM signal remains within the shutdown window for longer than the gate turn-off propagation delay of the previously conducting MOSFET, the output drivers are disabled and both MOSFET gates are pulled and held low. The shutdown state is removed when the PWM signal moves outside the shutdown window. The PWM rising and falling thresholds outlined in the “Electrical Specifications” on [page 7](#) determine when the lower and upper gates are enabled. During normal operation in a typical application, the PWM rise and fall times through the shutdown window should not exceed either output’s turn-off propagation delay plus the MOSFET gate discharge time to $\sim 1V$. Abnormally long PWM signal transition times through the shutdown window will simply introduce additional dead time between turn off and turn on of the synchronous bridge’s MOSFETs. For optimal performance, no more than 50pF parasitic capacitive load should be present on the PWM line of the HIP2106A (assuming a Renesas PWM controller is used).

3.2 HI/LI Inputs (HIP2105)

Designed for high speed switching, the HIP2105 MOSFET driver controls both high-side and low-side N-channel FETs from two externally provided HI and LI signals. The external signal source in this case will provide the required dead time control

A falling transition on LI initiates the turn-off of the lower MOSFET (see [Figure 5 on page 8](#)). After a short propagation delay (t_{PDFL}), the lower gate begins to fall. Typical fall times (t_{FL}) are provided in the “Electrical Specifications” table on [page 7](#). After an externally set dead time the HI will initiate the turn on of the upper MOSFET, after a short propagation delay (t_{PDRH}) the UGATE begins to rise with rise time given by (t_{RH}). At the end

of the high-side on-time the HI will initiate a fall, after a propagation delay of (t_{PDFH}) the UGATE will turn off with a fall time (t_{FH}). Once the UGATE is off and the dead time has elapsed, the LGATE turn on is initiated by the LI input with a propagation delay of (t_{PDRL}) and the cycle repeats. However, by internal hardwired logic if both HI and LI are high or low the UGATE and LGATE outputs remain in the low state to prevent a shoot-through condition. Additionally, if one of the inputs is high and the other input goes high, any output that is high transitions low to prevent a shoot-through condition.

3.3 Bootstrap Considerations

This driver features an internal bootstrap diode. Simply adding an external capacitor across the BOOT and PHASE pins completes the bootstrap circuit.

[Equation 1](#) helps select a proper bootstrap capacitor size:

$$(EQ. 1) \quad C_{BOOT_CAP} \geq \frac{Q_{GATE}}{\Delta V_{BOOT_CAP}}$$

$$Q_{GATE} = \frac{Q_{G1} \cdot V_{CC}}{V_{GS1}} \cdot N_{Q1}$$

where Q_{G1} is the amount of gate charge per upper MOSFET at V_{GS1} gate-source voltage and N_{Q1} is the number of control MOSFETs. The ΔV_{BOOT_CAP} term is defined as the allowable droop in the rail of the upper gate drive.

As an example, suppose two IRLR7821 FETs are chosen as the upper MOSFETs. The gate charge, Q_G , from the datasheet is 10nC at 4.5V (V_{GS}) gate-source voltage. Then the Q_{GATE} is calculated to be 22nC at V_{CC} levels. assuming a 200mV droop in drive voltage over the PWM cycle. A bootstrap capacitance of at least 0.110μF is required. The next larger standard value capacitance is 0.22μF. A good quality ceramic capacitor is recommended.

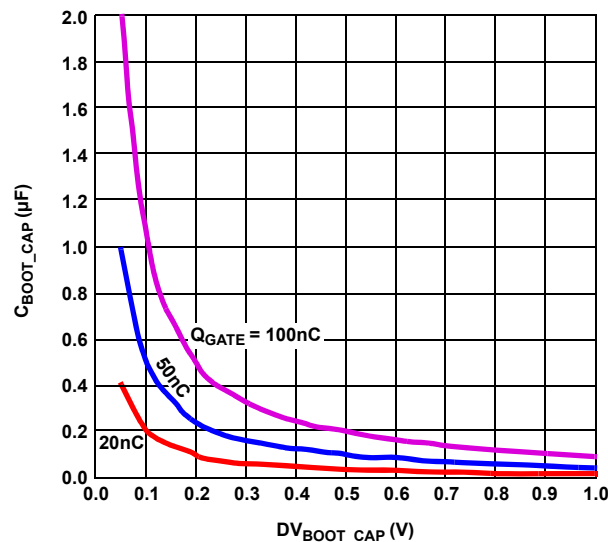


Figure 8. Bootstrap Capacitance vs Boot Ripple Voltage

3.4 Power Dissipation

Package power dissipation is mainly a function of the switching frequency (f_{SW}), the output drive impedance, the external gate resistance, and the selected MOSFET's internal gate resistance and total gate charge. Calculating the power dissipation in the driver for a desired application is critical to ensure safe operation. Exceeding the maximum allowable power dissipation level will push the IC beyond the maximum recommended operating junction temperature of +125°C. See "[Layout Considerations](#)" on page 13 for thermal transfer improvement suggestions. When designing the driver into an application, it is recommended that the following calculation is used to ensure safe operation at the desired frequency for the selected MOSFETs. The total gate drive power losses

due to the gate charge of MOSFETs and the driver's internal circuitry and their corresponding average driver current can be estimated with [Equations 2](#) and [3](#), respectively:

$$(EQ. 2) \quad P_{Qg_TOT} = P_{Qg_Q1} + P_{Qg_Q2} + I_Q \cdot V_{CC}$$

$$P_{Qg_Q1} = \frac{Q_{G1} \cdot V_{CC}^2}{V_{GS1}} \cdot f_{SW} \cdot N_{Q1}$$

$$P_{Qg_Q2} = \frac{Q_{G2} \cdot V_{CC}^2}{V_{GS2}} \cdot f_{SW} \cdot N_{Q2}$$

$$(EQ. 3) \quad I_{VCC} = \left(\frac{Q_{G1} \cdot N_{Q1}}{V_{GS1}} + \frac{Q_{G2} \cdot N_{Q2}}{V_{GS2}} \right) \cdot V_{CC} \cdot f_{SW} + I_Q$$

where the gate charge (Q_{G1} and Q_{G2}) is defined at a particular gate-to-source voltage (V_{GS1} and V_{GS2}) in the corresponding MOSFET datasheet; I_Q is the driver's total quiescent current with no load at both drive outputs; N_{Q1} and N_{Q2} are the number of upper and lower MOSFETs, respectively. The $I_Q V_{CC}$ product is the quiescent power of the driver without capacitive load and is typically negligible.

The total gate drive power losses are dissipated among the resistive components along the transition path. The drive resistance dissipates a portion of the total gate drive power losses, the rest will be dissipated by the external gate resistors (R_{G1} and R_{G2} , should be a short to avoid interfering with the operation shoot-through protection circuitry) and the internal gate resistors (R_{GI1} and R_{GI2}) of MOSFETs. [Figures 9](#) and [10](#) show the typical upper and lower gate drives turn-on transition path. The power dissipation on the driver can be roughly estimated as:

$$(EQ. 4) \quad P_{DR} = P_{DR_UP} + P_{DR_LOW} + I_Q \cdot V_{CC}$$

$$P_{DR_UP} = \left(\frac{R_{HI1}}{R_{HI1} + R_{EXT1}} + \frac{R_{LO1}}{R_{LO1} + R_{EXT1}} \right) \cdot \frac{P_{Qg_Q1}}{2}$$

$$P_{DR_LOW} = \left(\frac{R_{HI2}}{R_{HI2} + R_{EXT2}} + \frac{R_{LO2}}{R_{LO2} + R_{EXT2}} \right) \cdot \frac{P_{Qg_Q2}}{2}$$

$$R_{EXT1} = R_{G1} + \frac{R_{GI1}}{N_{Q1}} \quad R_{EXT2} = R_{G2} + \frac{R_{GI2}}{N_{Q2}}$$

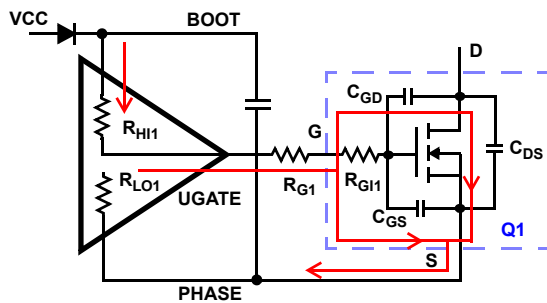


Figure 9. Typical Upper-Gate Drive Turn-On Path

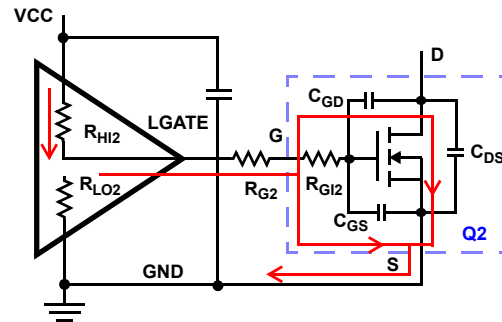


Figure 10. Typical Lower-Gate Drive Turn-On Path

4. Application Information

4.1 MOSFET Selection

The parasitic inductances of the PCB and of the power devices' packaging (both upper and lower MOSFETs) can cause serious ringing, exceeding absolute maximum rating of the devices. The negative ringing at the edges of the PHASE node could increase the bootstrap capacitor voltage through the internal bootstrap diode, and in some cases, it may overstress the upper MOSFET driver. Careful layout, proper selection of MOSFETs, and packaging can go a long way toward minimizing such unwanted stress.

The D²-PAK, or D-PAK packaged MOSFETs, have large parasitic lead inductances and are not recommended unless additional circuits are implemented to prevent the BOOT and PHASE pins from exceeding the device rating. Low-profile MOSFETs, such as direct FETs and multi-source leads devices (SO-8, LPAK, PowerPAK), have low parasitic lead inductances and are preferred.

4.2 Layout Considerations

A good layout helps reduce the ringing on the switching node (PHASE) and significantly lowers the stress applied to the output drives. Use the following advice for an optimized layout:

- Keep decoupling loops (VCC - GND and BOOT - PHASE) as short as possible.
- Minimize trace inductance, especially on low-impedance lines. All power traces (UGATE, PHASE, LGATE, GND, VCC) should be short and wide, as much as possible.
- Minimize the inductance of the PHASE node. Ideally, place the source of the upper and the drain of the lower MOSFET as close as thermally allowable.
- Minimize the current loop of the output and input power trains. Short the source connection of the lower MOSFET to ground as close to the transistor pin as feasible. Place the input capacitors (especially ceramic decoupling) as close to the drain of the upper and source of the lower MOSFETs as possible.

In addition, for heat spreading, place copper underneath the IC whether it has an exposed pad or not. The copper area can be extended beyond the bottom area of the IC and/or connected to buried power ground plane(s) with thermal vias. This combination of vias for vertical heat escape, extended copper plane, and buried planes improve heat dissipation and allow the part to achieve its full thermal potential. [Figures 11](#) and [12](#) show a layout example.

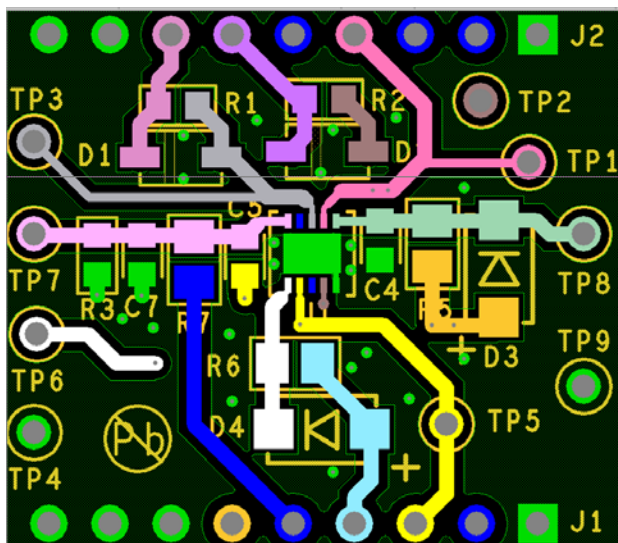


Figure 11. HIP2105DBEVAL1Z Top Layer

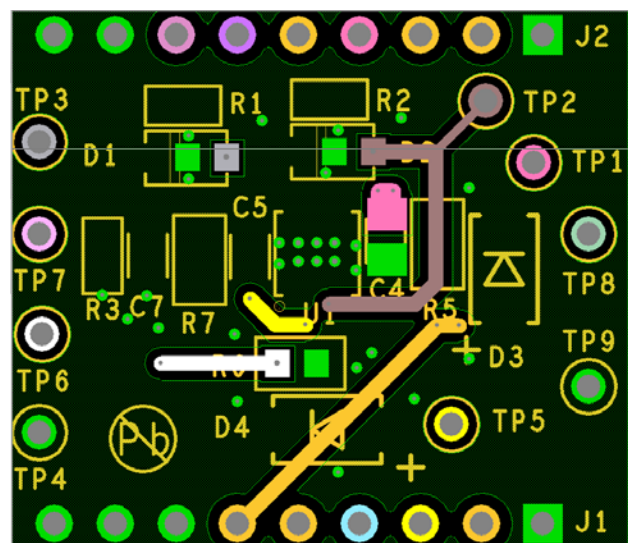


Figure 12. HIP2105DBEVAL1Z Bottom Layer

4.3 Upper MOSFET Self Turn-On Effects at Startup

If the driver has insufficient bias voltage applied, its outputs are floating. If the input bus is energized at a high dV/dt rate while the driver outputs are floating, because of self-coupling through the internal C_{GD} of the MOSFET, the UGATE could momentarily rise up to a level greater than the threshold voltage of the MOSFET. This could potentially turn on the upper switch and result in damaging inrush energy. Therefore, if such a situation (when input bus powered up before the bias of the controller and driver is ready) could conceivably be encountered, it is a common practice to place a resistor (R_{UGPH}) across the gate and source of the upper MOSFET to suppress the Miller coupling effect. The value of the resistor depends mainly on the input voltage's rate of rise, the C_{GD}/C_{GS} ratio, as well as the gate-source threshold of the upper MOSFET. A higher dV/dt , a lower C_{DS}/C_{GS} ratio, and a lower gate-source threshold upper FET will require a smaller resistor to diminish the effect of the internal capacitive coupling. For most applications, a 5k Ω to 10k Ω resistor is typically sufficient, not affecting normal performance and efficiency.

The coupling effect can be roughly estimated with [Equation 5](#), which assume a fixed linear input ramp and neglect the clamping effect of the body diode of the upper drive and the bootstrap capacitor. Other parasitic components such as lead inductances and PCB capacitances are also not taken into account. These equations are provided for guidance purpose only. Therefore, the actual coupling effect should be examined using a very high impedance (10M Ω or greater) probe to ensure a safe design margin.

$$(EQ. 5) \quad V_{GS_MILLER} = \frac{dV}{dt} \cdot R \cdot C_{rss} \left(1 - e^{\frac{-V_{DS}}{\frac{dV}{dt} \cdot R \cdot C_{iss}}} \right)$$

$$R = R_{UGPH} + R_{GI} \quad C_{rss} = C_{GD} \quad C_{iss} = C_{GD} + C_{GS}$$

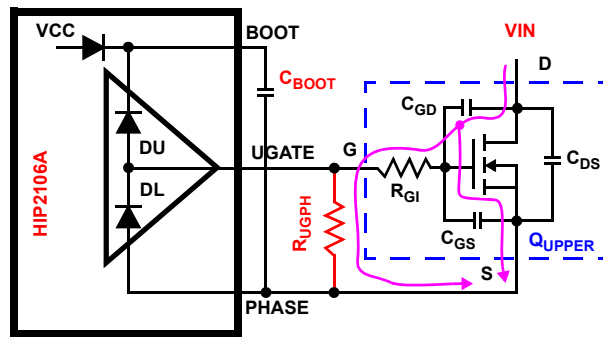


Figure 13. Gate-to-Source Resistor to Reduce Upper MOSFET Miller Coupling

5. Revision History

Rev.	Date	Description
1.00	Jun 6, 2018	Updated the first Features bullet and added the second one. In the second paragraph on page 1 changed 10ns to 15ns. Added the HIP2105 product information throughout datasheet. Updated Ordering information by adding Tape and Reel column and updating Note 1. Updated Pin descriptions for the UGATE and LGATE pins. Added CDM ESD and Latch-up Information Updated the Supply Voltage Maximum to 5.5V and added Minimum specification of 4.5V under "Recommended Operating Conditions" on page 6. Removed minimum value for the Maximum Operating Junction Temperature. Updated POR Falling typical from 3.0 to 3.1 Updated Hysteresis typical from 400 to 300 VIH and VIL Rising VDD = 4.5V Min changed from 1.22 to 1.3, Typ changed from 1.5 to 1.65, and max changed from 1.8 to 2V. VIH and VIL Rising VDD = 5.0 added Row VIH and VIL Rising VDD = 5.5V Min changed from 2.0 to 1.5, Typ changed from 2.4 to 1.9, and max changed from 2.7 to 2.2V. VIH and VIL Falling VDD = 4.5V Min changed from 0.8 to 0.9, Typ changed from 1.0 to 1.1, and max changed from 1.2 to 1.45V. VIH and VIL Falling VDD = 5.0V added Row VIH and VIL Falling VDD = 5.5V Min changed from 1.2 to 1.05, Typ changed from 1.5 to 1.3, and max changed from 1.7 to 1.65V. Added layout files to Layout Considerations section.
0.00	Jan 18, 2018	Initial release

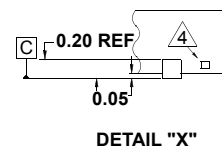
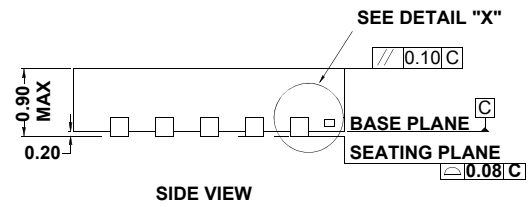
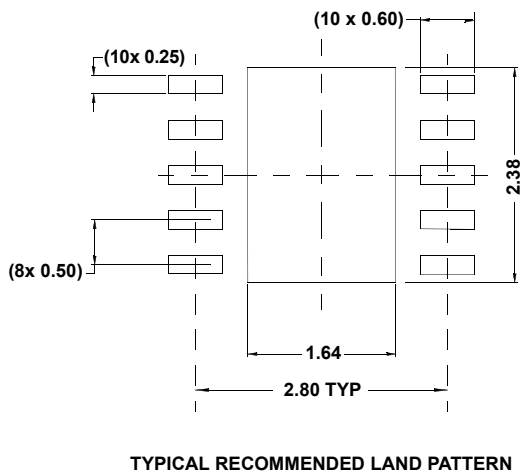
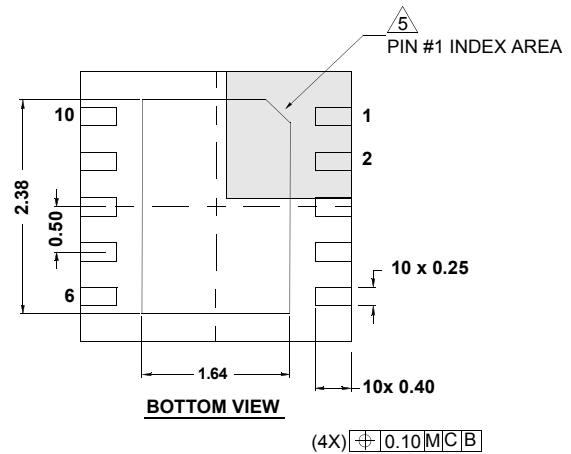
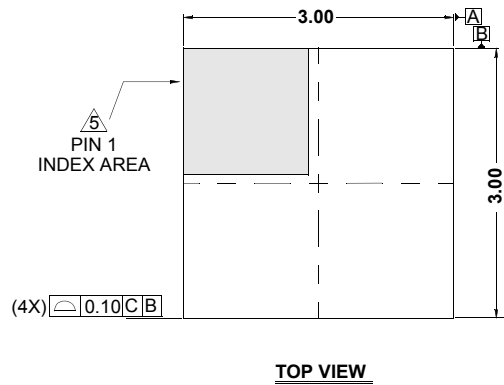
6. Package Outline Drawing

L10.3x3C

10 LEAD DUAL FLAT PACKAGE (DFN)

Rev 4, 3/15

For the most recent package outline drawing, see [L10.3x3C](#).



NOTES:

1. Dimensions are in millimeters.
Dimensions in () for Reference Only.
2. Dimensioning and tolerancing conform to AMSE Y14.5m-1994.
3. Unless otherwise specified, tolerance : Decimal ± 0.05
4. Tiebar shown (if present) is a non-functional feature and may be located on any of the 4 sides (or ends).
5. The configuration of the pin #1 identifier is optional, but must be located within the zone indicated. The pin #1 identifier may be either a mold or mark feature.
6. Compliant to JEDEC MO-229-WEED-3 except for E-PAD dimensions.

Notice

1. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation or any other use of the circuits, software, and information in the design of your product or system. Renesas Electronics disclaims any and all liability for any losses and damages incurred by you or third parties arising from the use of these circuits, software, or information.
 2. Renesas Electronics hereby expressly disclaims any warranties against and liability for infringement or any other claims involving patents, copyrights, or other intellectual property rights of third parties, by or arising from the use of Renesas Electronics products or technical information described in this document, including but not limited to, the product data, drawings, charts, programs, algorithms, and application examples.
 3. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or others.
 4. You shall not alter, modify, copy, or reverse engineer any Renesas Electronics product, whether in whole or in part. Renesas Electronics disclaims any and all liability for any losses or damages incurred by you or third parties arising from such alteration, modification, copying or reverse engineering.
 5. Renesas Electronics products are classified according to the following two quality grades: "Standard" and "High Quality". The intended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below.

"Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; industrial robots; etc.

"High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control (traffic lights); large-scale communication equipment; key financial terminal systems; safety control equipment; etc.

Unless expressly designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not intended or authorized for use in products or systems that may pose a direct threat to human life or bodily injury (artificial life support devices or systems; surgical implantations; etc.), or may cause serious property damage (space system; undersea repeaters; nuclear power control systems; aircraft control systems; key plant systems; military equipment; etc.). Renesas Electronics disclaims any and all liability for any damages or losses incurred by you or any third parties arising from the use of any Renesas Electronics product that is inconsistent with any Renesas Electronics data sheet, user's manual or other Renesas Electronics document.
 6. When using Renesas Electronics products, refer to the latest product information (data sheets, user's manuals, application notes, "General Notes for Handling and Using Semiconductor Devices" in the reliability handbook, etc.), and ensure that usage conditions are within the ranges specified by Renesas Electronics with respect to maximum ratings, operating power supply voltage range, heat dissipation characteristics, installation, etc. Renesas Electronics disclaims any and all liability for any malfunctions, failure or accident arising out of the use of Renesas Electronics products outside of such specified ranges.
 7. Although Renesas Electronics endeavors to improve the quality and reliability of Renesas Electronics products, semiconductor products have specific characteristics, such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Unless designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not subject to radiation resistance design. You are responsible for implementing safety measures to guard against the possibility of bodily injury, injury or damage caused by fire, and/or danger to the public in the event of a failure or malfunction of Renesas Electronics products, such as safety design for hardware and software, including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult and impractical, you are responsible for evaluating the safety of the final products or systems manufactured by you.
 8. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. You are responsible for carefully and sufficiently investigating applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive, and using Renesas Electronics products in compliance with all these applicable laws and regulations. Renesas Electronics disclaims any and all liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
 9. Renesas Electronics products and technologies shall not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations. You shall comply with any applicable export control laws and regulations promulgated and administered by the governments of any countries asserting jurisdiction over the parties or transactions.
 10. It is the responsibility of the buyer or distributor of Renesas Electronics products, or any other party who distributes, disposes of, or otherwise sells or transfers the product to a third party, to notify such third party in advance of the contents and conditions set forth in this document.
 11. This document shall not be reprinted, reproduced or duplicated in any form, in whole or in part, without prior written consent of Renesas Electronics.
 12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products.
- (Note 1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its directly or indirectly controlled subsidiaries.
- (Note 2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.

(Rev.4.0-1 November 2017)



SALES OFFICES

Renesas Electronics Corporation

<http://www.renesas.com>

Refer to "<http://www.renesas.com/>" for the latest and detailed information.

Renesas Electronics America Inc.
1001 Murphy Ranch Road, Milpitas, CA 95035, U.S.A.
Tel: +1-408-432-8888, Fax: +1-408-434-5351

Renesas Electronics Canada Limited
9251 Yonge Street, Suite 8309 Richmond Hill, Ontario Canada L4C 9T3
Tel: +1-905-237-2004

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-651-700, Fax: +44-1628-651-804

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-6503-0, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
Room 1709 Quantum Plaza, No.27 ZhichunLu, Haidian District, Beijing, 100191 P. R. China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai, 200333 P. R. China
Tel: +86-21-2226-0888, Fax: +86-21-2226-0999

Renesas Electronics Hong Kong Limited
Unit 1601-1611, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2265-6688, Fax: +852-2886-9022

Renesas Electronics Taiwan Co., Ltd.
13F, No. 363, Fu Shing North Road, Taipei 10543, Taiwan
Tel: +886-2-8175-9600, Fax: +886-2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre, Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.
Unit 1207, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics India Pvt. Ltd.
No.777C, 100 Feet Road, HAL 2nd Stage, Indiranagar, Bangalore 560 038, India
Tel: +91-80-67208700, Fax: +91-80-67208777

Renesas Electronics Korea Co., Ltd.
17F, KAMCO Yangjae Tower, 262, Gangnam-daero, Gangnam-gu, Seoul, 06265 Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5338